



Features

- Wide bandgap SiC MOSFET technology
- Low On-Resistance with High Blocking Voltage
- Low Capacitances with High-Speed switching
- Low reverse recovery(Qrr)
- Halogen free, RoHs compliant

Benefits

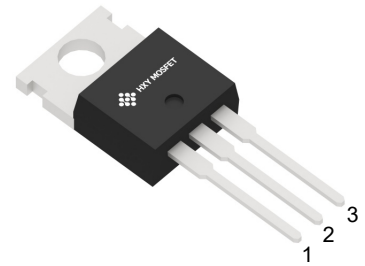
- Reduce switching losses
- Increased system Switching Frequency
- Increased power density
- Reduction of heat sink requirements

Applications

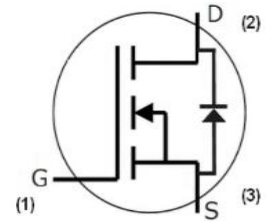
- Switch mode power supplies
- Renewable energy
- On Board Charger
- High Voltage DC/DC Converters



Ordering Part Number	Package	Brand
IPP65R280E6XKSA1	TO-220C	HXY MOSFET



TO-220C



Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Value	Unit	Note
V_{DSmax}	Drain-Source Voltage	$V_{GS} = 0V, I_D = 100\mu A$	650	V	
V_{GS}	Gate-Source voltage (transient)	$t_p \leq 500ns, \text{duty cycle} \leq 1\%$	-8/+20	V	
V_{GSop}	Recommend Gate-Source Voltage	Static	-4/+18	V	
EAS	Single pulse avalanche energy	$V_{DS}=650V, V_{DD}=50V, V_{GS}=10V, L=10mH, T_C=25^\circ\text{C}$	106	mJ	
I_D	Continuous Drain current	$V_{GS} = 18V, T_C = 25^\circ\text{C}$	9	A	Fig. 14
		$V_{GS} = 18V, T_C = 100^\circ\text{C}$	6.4		
$I_{D,pulse}$	Pulsed Drain Current	Pulse with t_p limited by T_{jmax}	17	A	
P_D	Power Dissipation	$T_C = 25^\circ\text{C}, T_j = 175^\circ\text{C}$	32	W	Fig. 16
T_j	Operating junction temperature		-55~175	$^\circ\text{C}$	
T_{stg}	Storage temperature		-55~175	$^\circ\text{C}$	



Thermal Characteristics

Symbol	Parameter	Value			Unit	Note
		Min.	Typ.	Max.		
$R_{th(jc)}$	Thermal resistance from Junction to Case		4.76		K/W	Fig. 15
$R_{th(ja)}$	Thermal resistance from Junction to Ambient		40		K/W	

Electrical Characteristics (T_c = 25°C unless other wise specified)

Static Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$V_{(BR)DSS}$	Drain-Source Breakdown voltage	$V_{GS} = 0V, I_D = 100\mu A$	650			V	
$V_{GS(th)}$	Gate Threshold voltage	$V_{GS} = V_{DS}, I_D = 1.33mA$		2.7		V	Fig. 9
		$V_{GS} = V_{DS}, I_D = 1.33mA, T_J = 175^\circ C$		1.8			
I_{GSS}	Gate-Source Leakage current	$V_{GS} = 18V, V_{DS} = 0V$			250	nA	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 650V, V_{GS} = 0V, T_J = 25^\circ C$		1	50	μA	
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS} = 15V, I_D = 4.5A$		320	390	m Ω	Fig. 3, 4, 5
		$V_{GS} = 18V, I_D = 4.5A$		260			
		$V_{GS} = 15V, I_D = 4.5A, T_J = 175^\circ C$ $V_{GS} = 18V, I_D = 4.5A, T_J = 175^\circ C$		400 360			
g_{fs}	Transconductance	$V_{DS} = 18V, I_D = 4.5A$		4		S	Fig. 6
		$V_{DS} = 18V, I_D = 4.5A, T_J = 175^\circ C$		3			



Gate Charge Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
Q_{GS}	Gate to Source Charge	$V_{DS} = 400V$ $I_D = 4.5A$ $V_{GS} = -4V/18V$		2.5		nC	Fig. 10
Q_{GD}	Gate to Drain Charge			6			
Q_G	Total Gate Charge			11.6			

AC Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
C_{iss}	Input Capacitance	$V_{GS} = 0V, V_{DS} = 600V$ $f = 1\text{ MHz}$ $V_{AC} = 25mV$		184		pF	Fig. 13
C_{oss}	Output Capacitance			22		pF	
C_{rss}	Reverse Transfer Capacitance			3.2		pF	
$R_{G(int)}$	Internal Gate Resistance	$f = 1\text{ MHz}, V_{AC} = 25mV$		13		Ω	



Reverse Diode Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
V_{SD}	Diode Forward Voltage	$V_{GS} = -4V, I_{SD} = 2.5A$		4.2		V	Fig. 7,8
		$V_{GS} = -4V, I_{SD} = 2.5A, T_j = 175^{\circ}C$		3.9			
I_S	Continuous Diode Forward Current	$V_{GS} = -4V, T_C = 25^{\circ}C$		6		A	
$I_{S, pulse}$	Diode pulse Current	$V_{GS} = -4V$, pulse width t_p limited by T_{jmax}		17		A	
t_{rr}	Reverse Recovery Time	$V_{GS} = -4V, I_{SD} = 4.5A, V_R = 400V$ $diff/dt = 1000A/us$		23		nS	
Q_{rr}	Reverse Recovery Charge			34		nC	
I_{rm}	Peak Reverse Recovery Current			3.4		A	

Switching Characteristics

Symbol	Parameter	Test conditions	Value			Unit	Note
			Min.	Typ.	Max.		
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 400V, V_{GS} = -4/+18V$ $I_D = 4.5A, R_{G(ext)} = 20\Omega$ $L = 833\mu H$		1		nS	Fig.21
t_r	Rise Time			14		nS	
$t_{d(off)}$	Turn-Off Delay Time			8		nS	
t_f	Fall Time			10		nS	
E_{on}	Turn-On Energy			20		μJ	Fig.19
E_{off}	Turn-Off Energy			12		μJ	
E_{tot}	Total switching energy			32		μJ	



Typical Performance

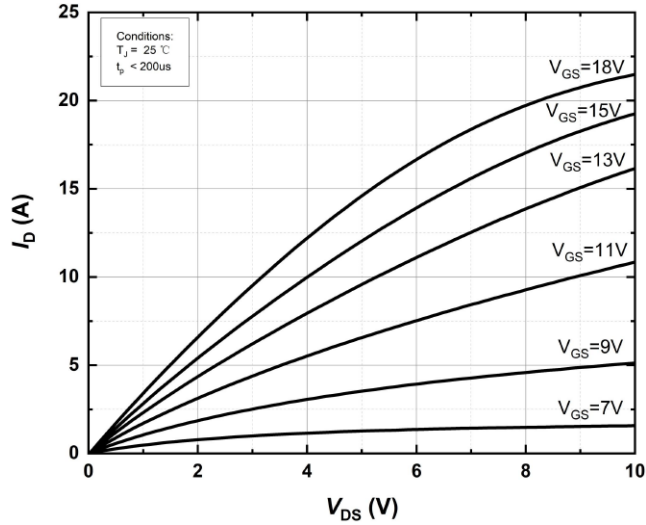


Figure 1. Output characteristics at $T_j=25^\circ\text{C}$

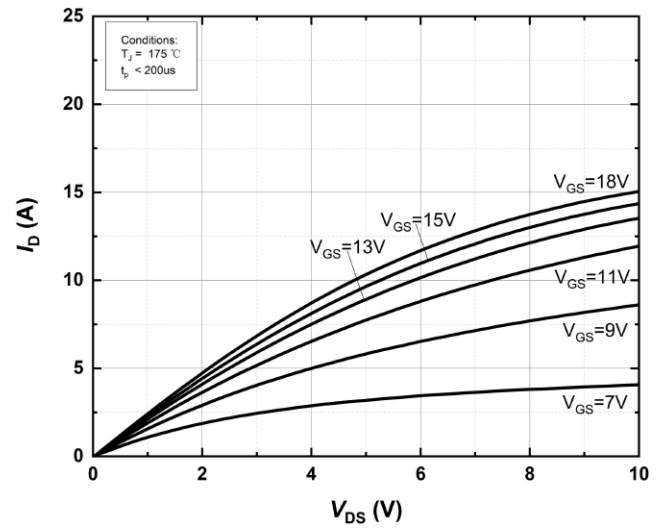


Figure 2. Output characteristics at $T_j=175^\circ\text{C}$

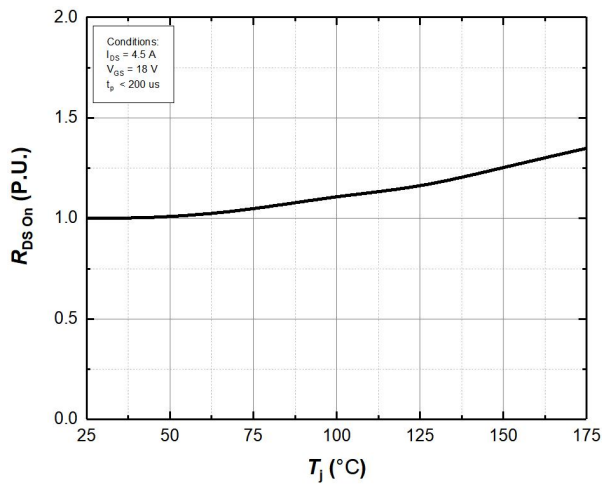


Figure 3. Normalized On-Resistance vs. Temperature

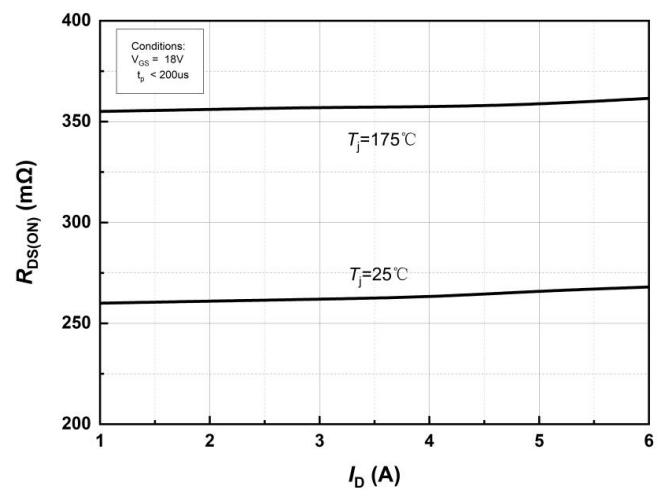


Figure 4. On-Resistance vs. Drain current for Various Temperature

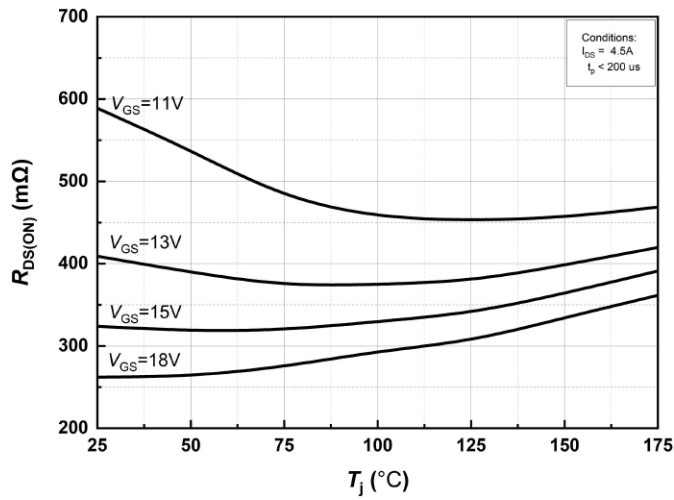


Figure 5. On-Resistance vs. Temperature for Various Gate Voltage

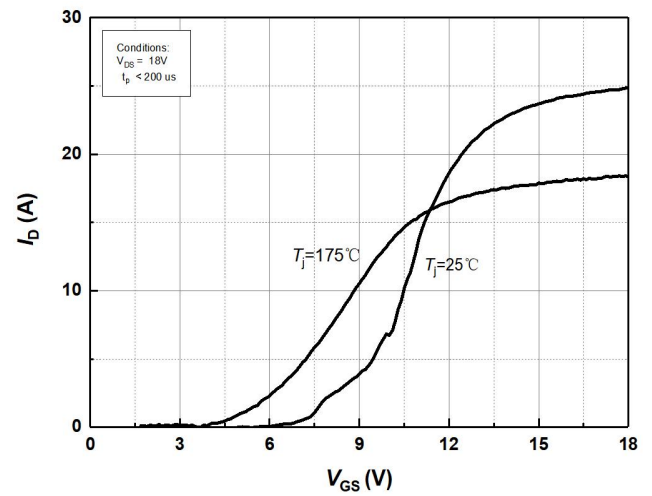


Figure 6. Transfer Characteristics for Various Junction Temperatures

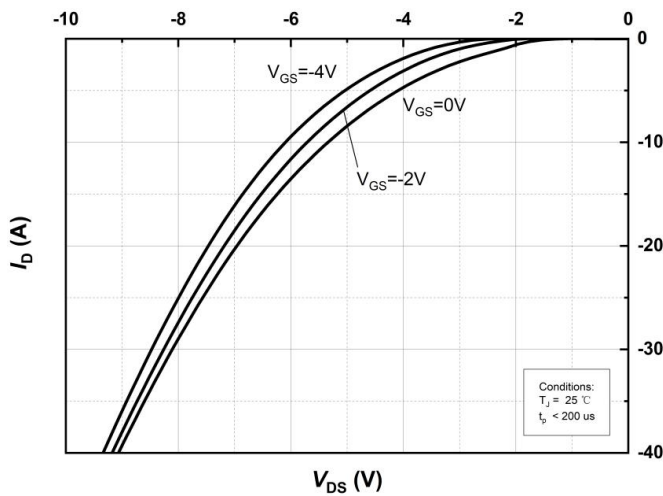


Figure 7. Body Diode Characteristics at $T_J=25^{\circ}C$

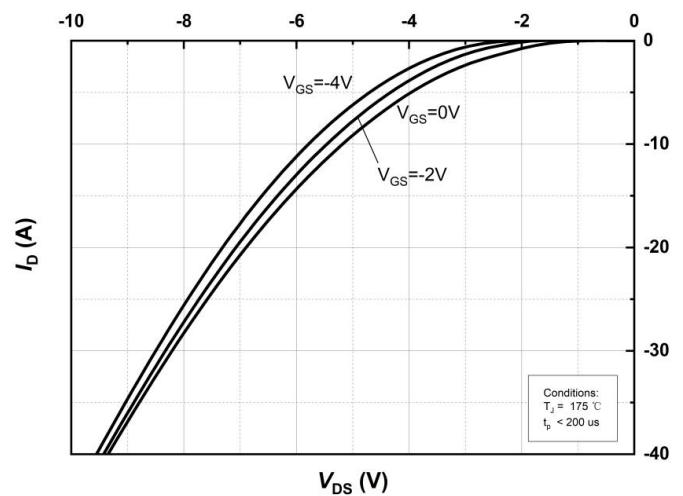


Figure 8. Body Diode Characteristics at $T_J=175^{\circ}C$

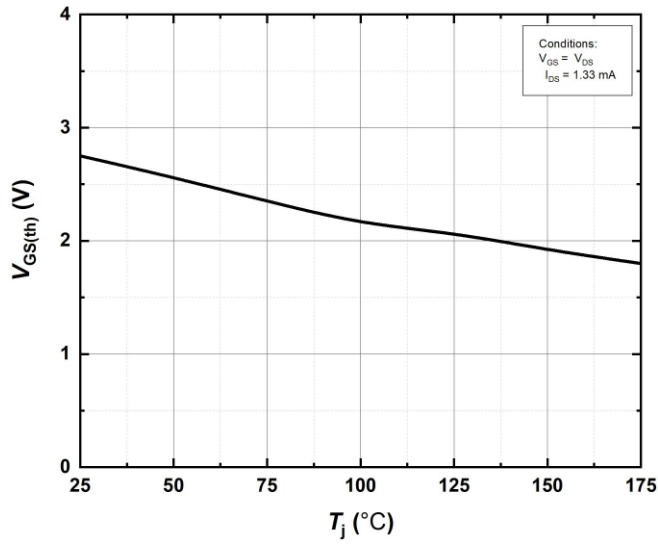


Figure 9. Threshold Voltage vs. Temperature

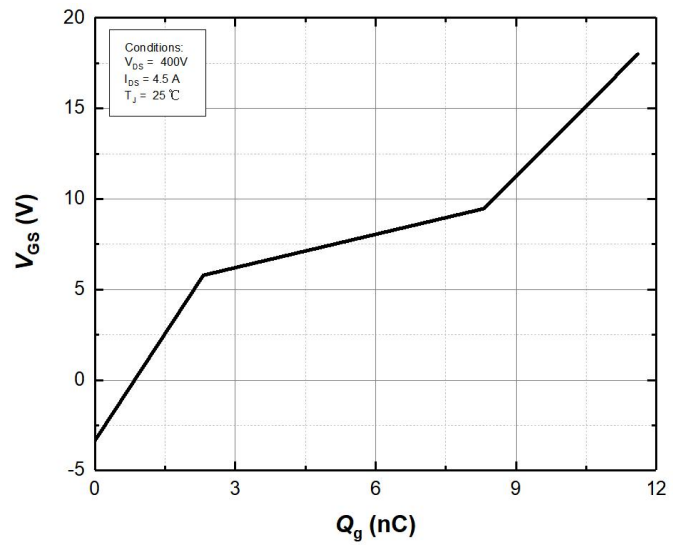


Figure 10 Gate Charge Characteristics

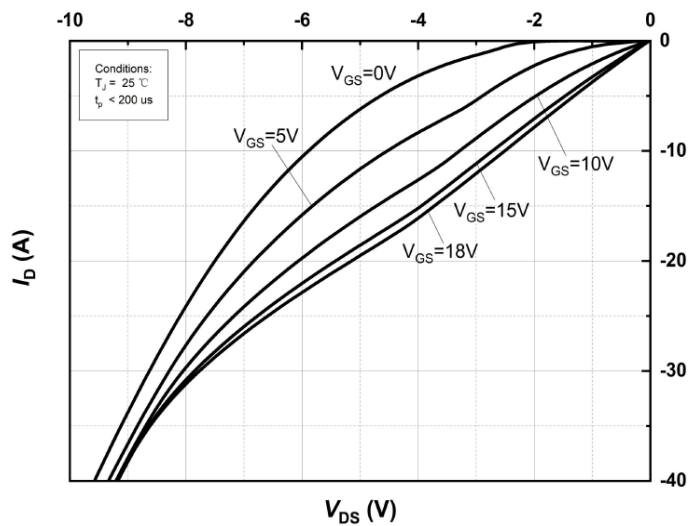


Figure 11. 3rd Quadrant Characteristic at $T_J=25^\circ \text{C}$

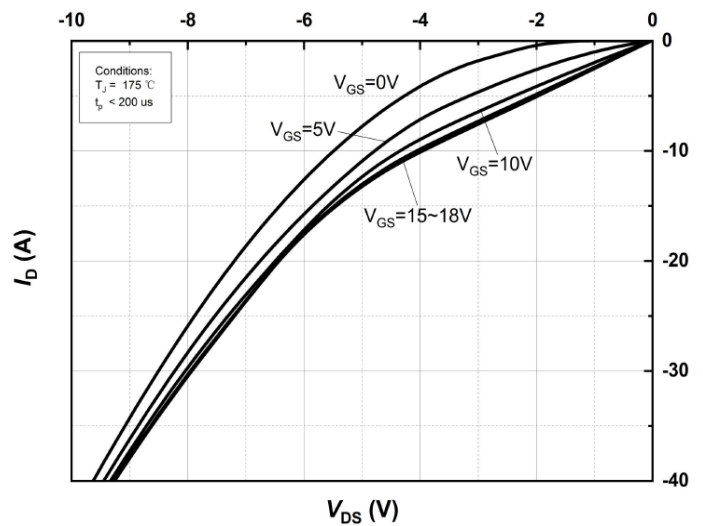


Figure 12. 3rd Quadrant Characteristic at $T_J=175^\circ \text{C}$

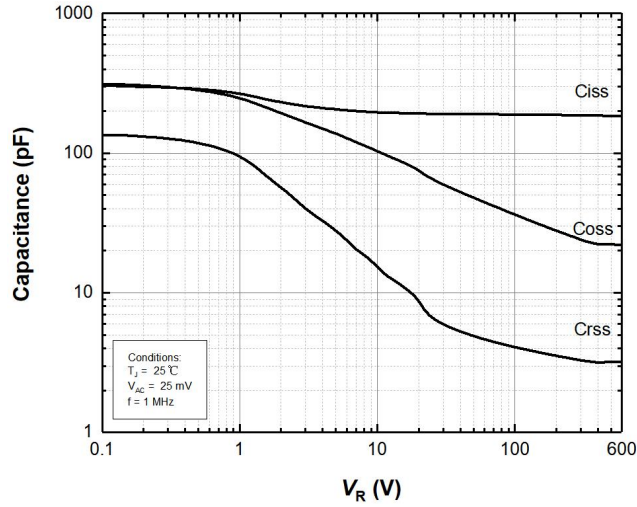


Figure 13. Capacitances vs. Drain-Source Voltage (0 – 600V)

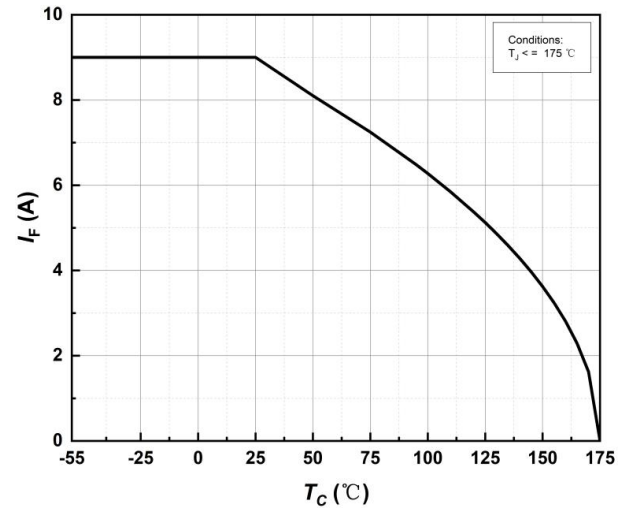


Figure 14. Continuous Drain Current Derating vs Case Temperature

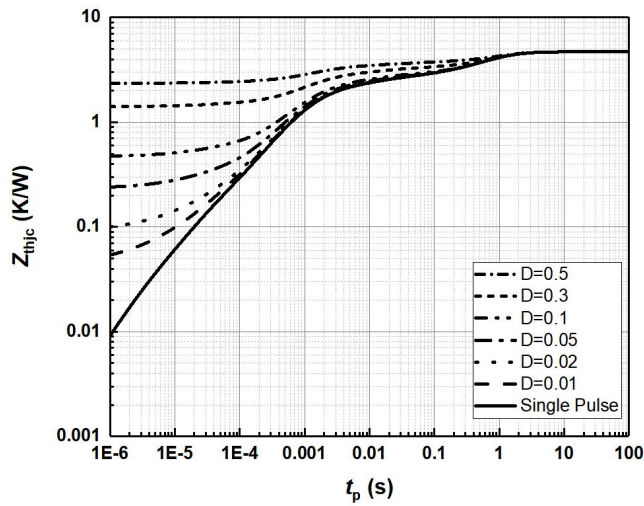


Figure 15. Transient Thermal Impedance (Junction – Case)

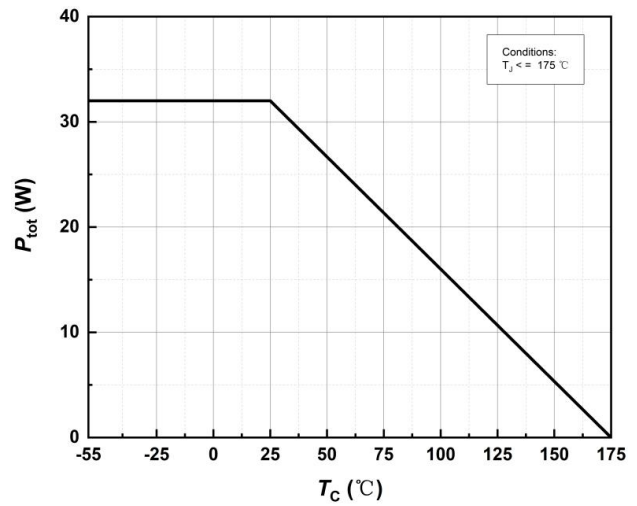


Figure 16. Maximum Power Dissipation Derating vs. Case Temperature

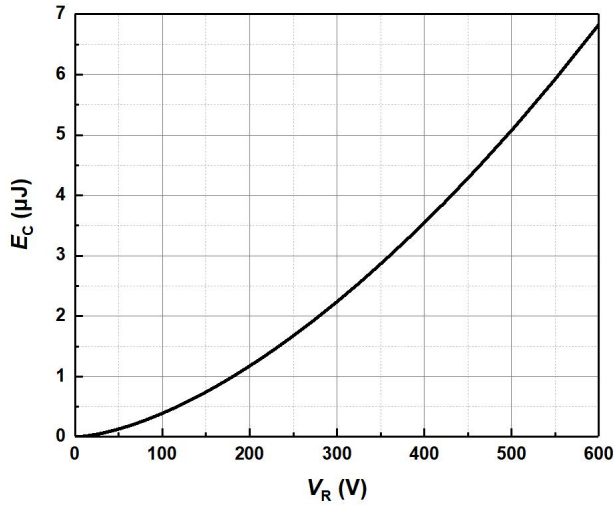


Figure 17. Output Capacitor Stored Energy

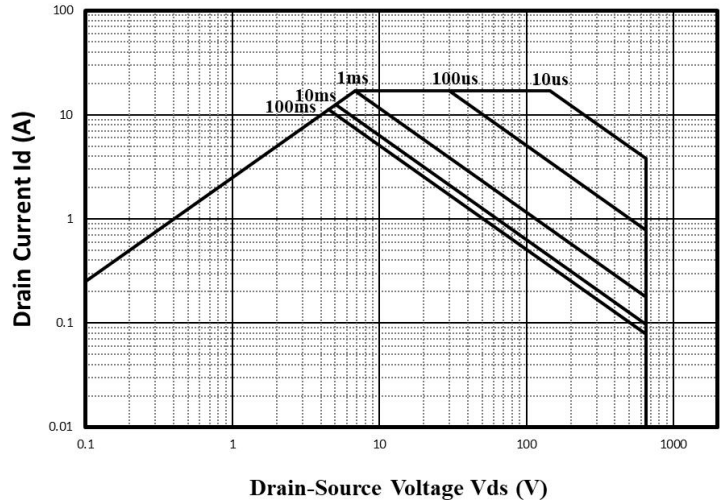


Figure 18. Safe Operating Area

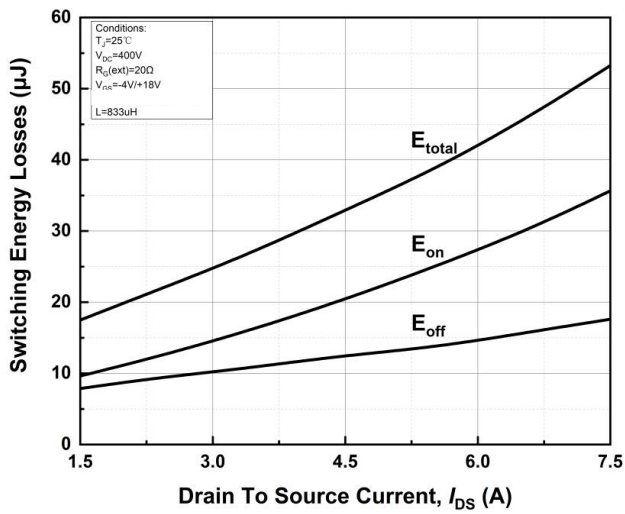


Figure 19. Clamped Inductive Switching Energy vs. Drain Current($V_{DD} = 400\text{V}$)

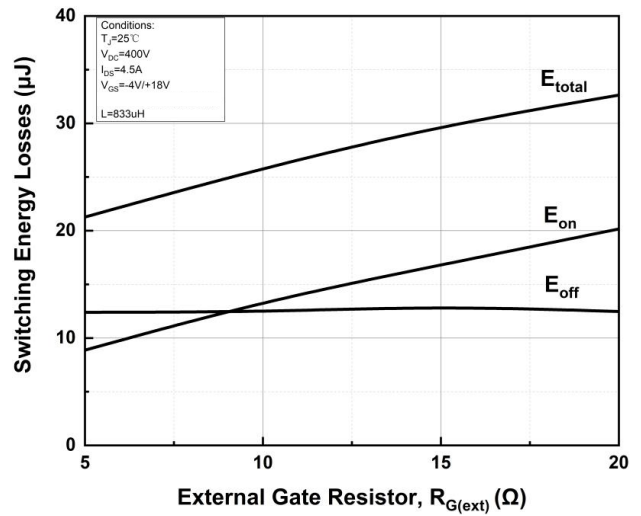


Figure 20. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

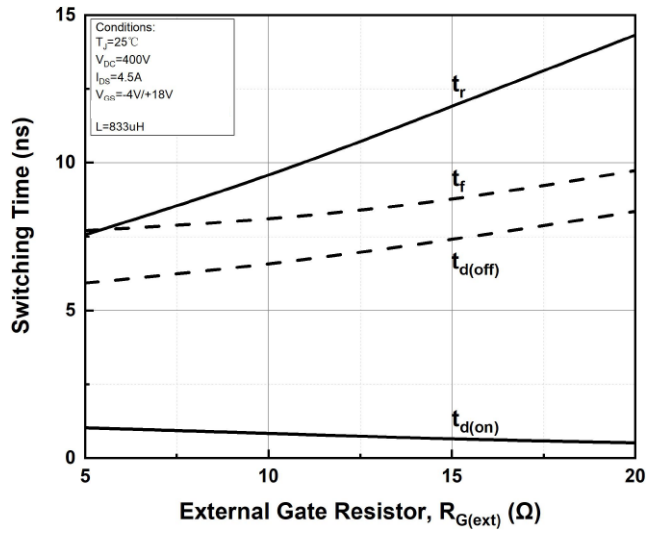
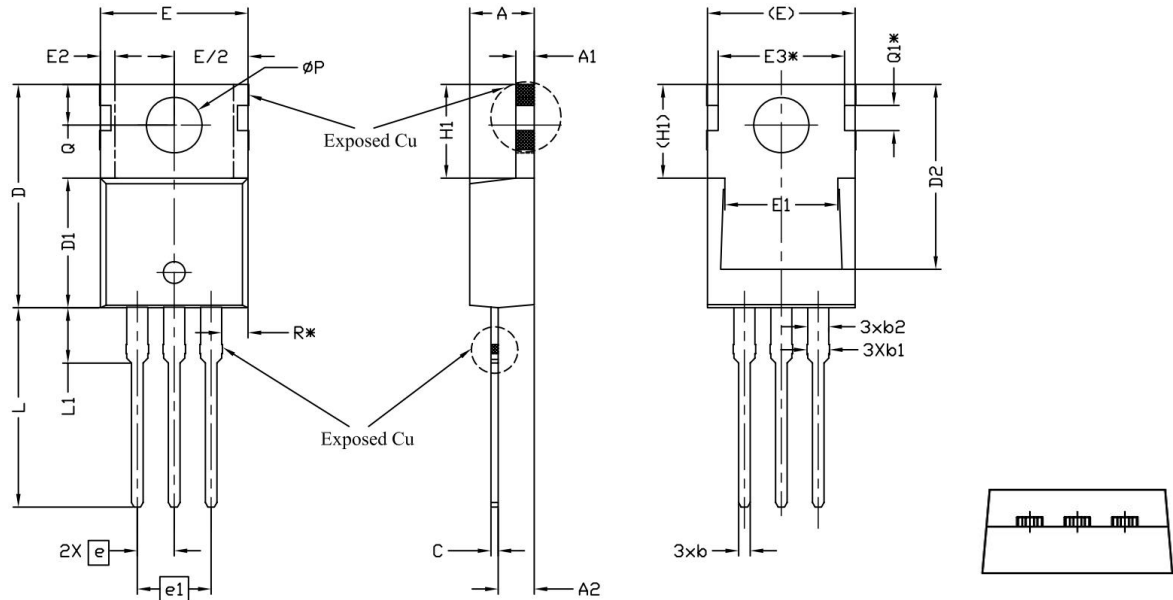


Figure 21. Switching Times vs. $R_{G(\text{ext})}$

Package Dimensions

Package TO-220C



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.43	12.73	12.83	5
E	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E2	-	-	0.76	6
E3*	8.70REF.			
e	2.54BSC			
e1	5.08BSC			
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
ØP	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73REF.			
R*	1.82REF.			



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